



**THE DATASHEET OF  
NTD5802NT4G**



# NTD5802N, NVD5802N

## MOSFET – Power, Single, N-Channel, DPAK 40 V, 101 A

### Features

- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- MSL 1/260°C
- 100% Avalanche Tested
- NVD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

### Applications

- CPU Power Delivery
- DC-DC Converters
- Motor Driver

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit		
Drain-to-Source Voltage	$V_{DSS}$	40	V		
Gate-to-Source Voltage	$V_{GS}$	$\pm 20$	V		
Continuous Drain Current ( $R_{\theta JC}$ ) (Note 1)	$I_D$	$T_C = 25^\circ\text{C}$	101	A	
		$T_C = 85^\circ\text{C}$	78		
Power Dissipation ( $R_{\theta JC}$ ) (Note 1)	$P_D$	$T_C = 25^\circ\text{C}$	93.75	W	
		$T_A = 25^\circ\text{C}$	16.4	A	
Continuous Drain Current ( $R_{\theta JA}$ ) (Note 1)	$I_D$	$T_A = 25^\circ\text{C}$	16.4	A	
		$T_A = 85^\circ\text{C}$	12.7		
Power Dissipation ( $R_{\theta JA}$ ) (Note 1)	$P_D$	$T_A = 25^\circ\text{C}$	2.5	W	
		$T_A = 25^\circ\text{C}$	2.5		
Pulsed Drain Current	$t_p = 10\mu\text{s}$	$T_A = 25^\circ\text{C}$	$I_{DM}$	300	A
Current Limited by Package	$T_A = 25^\circ\text{C}$	$I_{DmaxPkg}$	45	A	
Operating Junction and Storage Temperature	$T_J, T_{stg}$	-55 to 175		$^\circ\text{C}$	
Source Current (Body Diode)	$I_S$	50		A	
Drain to Source dV/dt	dV/dt	6.0		V/ns	
Single Pulse Drain-to-Source Avalanche Energy ( $V_{DD} = 32\text{ V}$ , $V_{GS} = 10\text{ V}$ , $L = 0.3\text{ mH}$ , $I_{L(pk)} = 40\text{ A}$ , $R_G = 25\ \Omega$ )	$E_{AS}$	240		mJ	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	$T_L$	260		$^\circ\text{C}$	

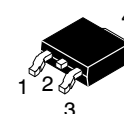
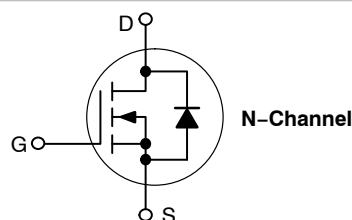
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



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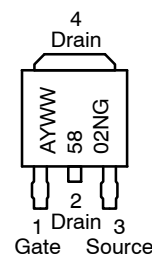
<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(on)}$	$I_D$
40 V	4.4 m $\Omega$ @ 10 V	101 A
	7.8 m $\Omega$ @ 5.0 V	50 A



CASE 369C  
DPAK  
(Bent Lead)  
STYLE 2

### MARKING DIAGRAMS & PIN ASSIGNMENT



A = Assembly Location\*  
Y = Year  
WW = Work Week  
5802N = Device Code  
G = Pb-Free Package

\* The Assembly Location code (A) is front side optional. In cases where the Assembly Location is stamped in the package, the front side assembly code may be blank.

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

# NTD5802N, NVD5802N

## Thermal Resistance Maximum Ratings

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	$R_{\theta JC}$	1.6	°C/W
Junction-to-Ambient - Steady State (Note 1)	$R_{\theta JA}$	60	
Junction-to-Ambient - Steady State (Note 2)	$R_{\theta JA}$	105	

- Surface-mounted on FR4 board using 1 in sq pad size, 1 oz Cu.
- Surface-mounted on FR4 board using the minimum recommended pad size.

## Electrical Characteristics ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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### Off Characteristics

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 10\ \mu\text{A}$	40			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			40		mV/°C
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0\text{ V}, V_{DS} = 40\text{ V}$	$T_J = 25^\circ\text{C}$		1.0	$\mu\text{A}$
			$T_J = 150^\circ\text{C}$		50	
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA

### On Characteristics (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\ \mu\text{A}$	1.5		3.5	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			-7.4		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 50\text{ A}$		3.6	4.4	m $\Omega$
		$V_{GS} = 5.0\text{ V}, I_D = 50\text{ A}$		6.5	7.8	
Forward Transconductance	gFS	$V_{DS} = 15\text{ V}, I_D = 15\text{ A}$		16.8		S

### Charges and Capacitances

Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = 12\text{ V}$		5300		pF
Output Capacitance	$C_{oss}$			850		
Reverse Transfer Capacitance	$C_{rss}$			550		
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = 25\text{ V}$		5025		pF
Output Capacitance	$C_{oss}$			580		
Reverse Transfer Capacitance	$C_{rss}$			400		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V}, I_D = 50\text{ A}$		75	100	nC
Threshold Gate Charge	$Q_{G(TH)}$			6.0		
Gate-to-Source Charge	$Q_{GS}$			18		
Gate-to-Drain Charge	$Q_{GD}$			15		

### Switching Characteristics (Note 4)

Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 20\text{ V}, I_D = 50\text{ A}, R_G = 2.0\ \Omega$		14		ns
Rise Time	$t_r$			52		
Turn-Off Delay Time	$t_{d(off)}$			39		
Fall Time	$t_f$			8.5		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2\%$ .
- Switching characteristics are independent of operating junction temperatures.

## NTD5802N, NVD5802N

### ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise noted) (continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>DRAIN-SOURCE DIODE CHARACTERISTICS</b>						
Forward Diode Voltage	$V_{SD}$	$V_{GS} = 0\text{ V},$ $I_S = 50\text{ A}$		0.9	1.2	V
		$V_{GS} = 0\text{ V},$ $I_S = 20\text{ A}$		0.8	1.0	
Reverse Recovery Time	$t_{RR}$	$V_{GS} = 0\text{ V},$ $dI_S/dt = 100\text{ A}/\mu\text{s},$ $I_S = 50\text{ A}$		25		ns
Charge Time	$t_a$			15		
Discharge Time	$t_b$			10		
Reverse Recovery Charge	$Q_{RR}$			15		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

4. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CHARACTERISTICS

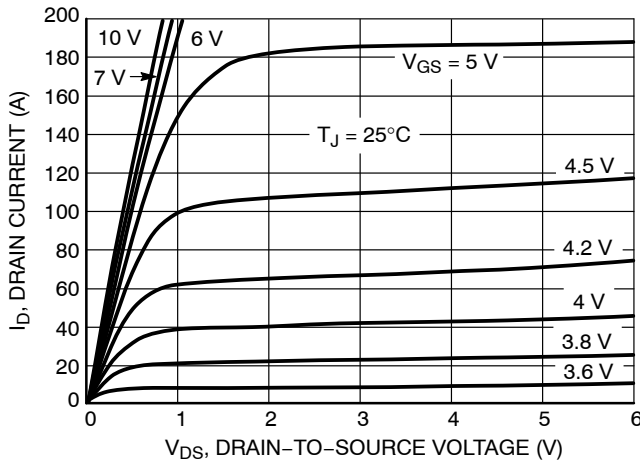


Figure 1. On-Region Characteristics

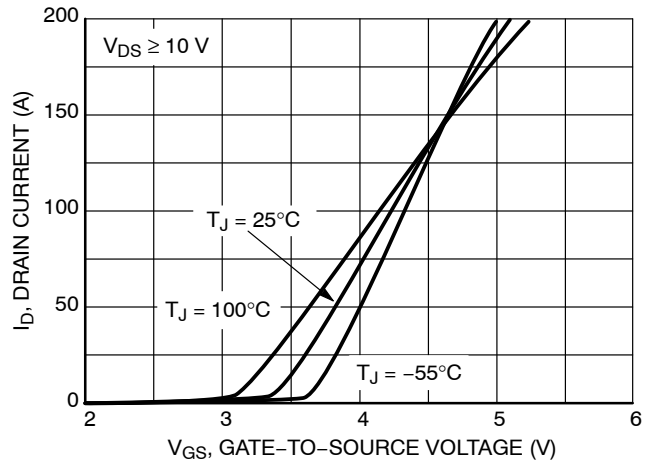


Figure 2. Transfer Characteristics

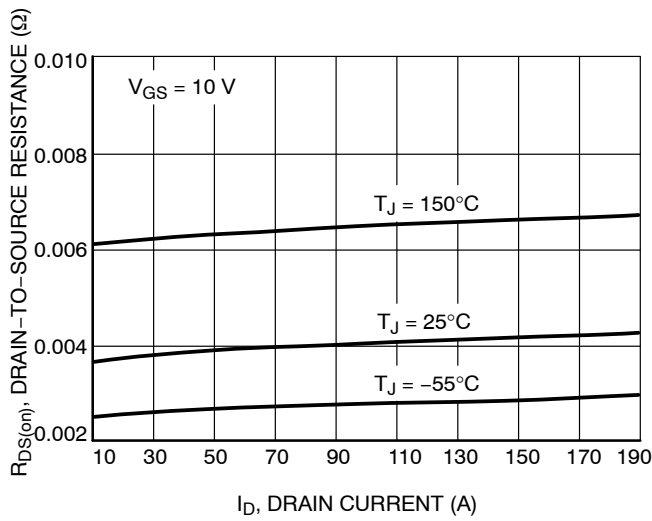


Figure 3. On-Resistance vs. Drain Current

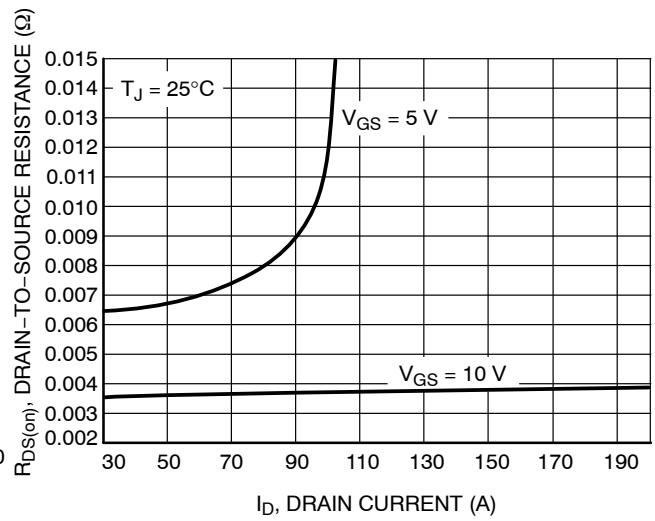


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

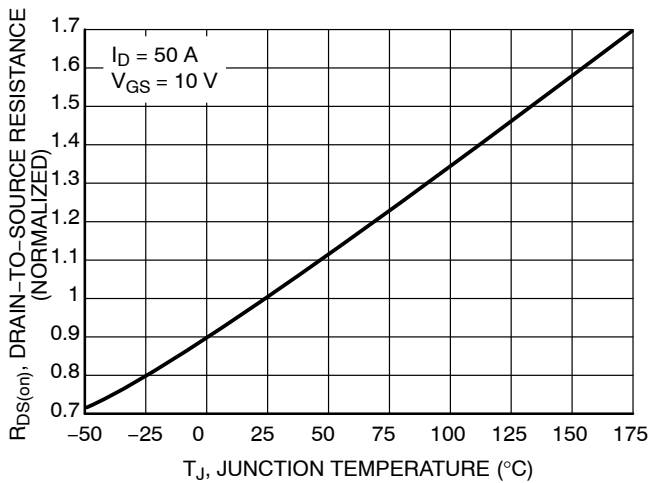


Figure 5. On-Resistance Variation with Temperature

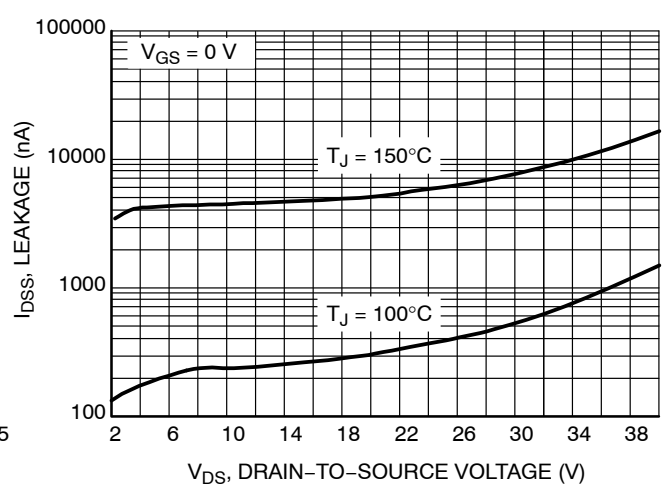


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CHARACTERISTICS

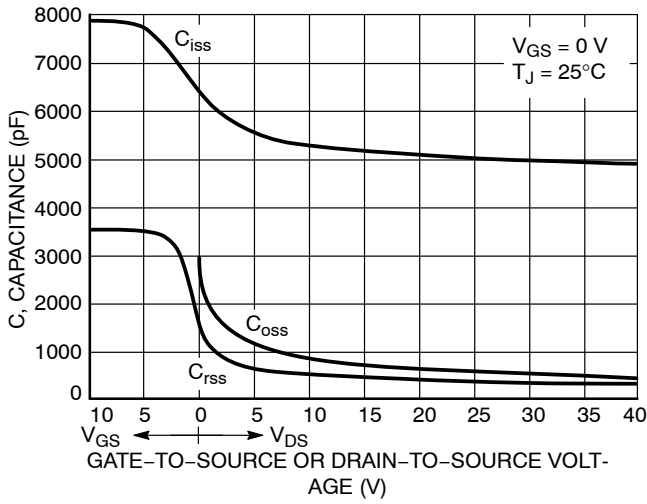


Figure 7. Capacitance Variation

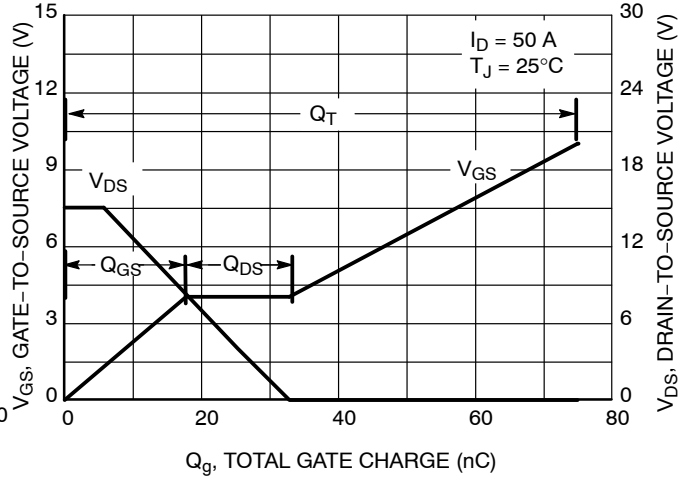


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

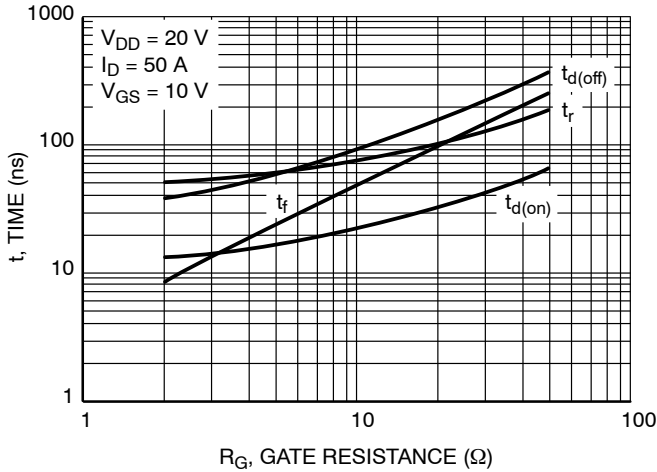


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

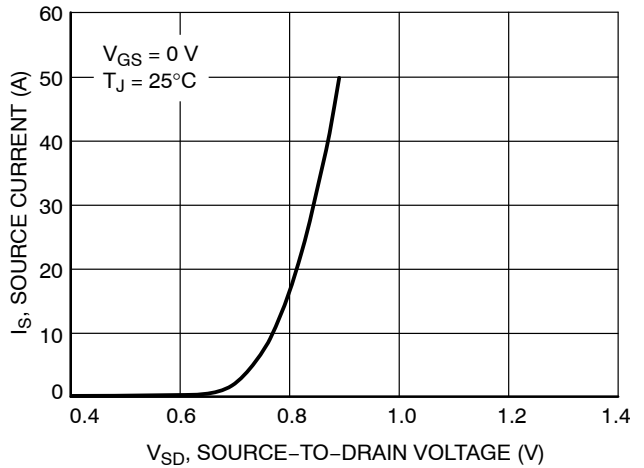


Figure 10. Diode Forward Voltage vs. Current

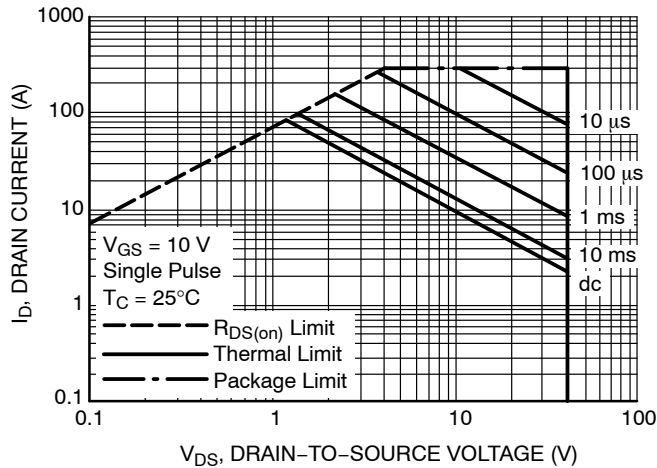


Figure 11. Maximum Rated Forward Biased Safe Operating Area

# NTD5802N, NVD5802N

## TYPICAL PERFORMANCE CHARACTERISTICS

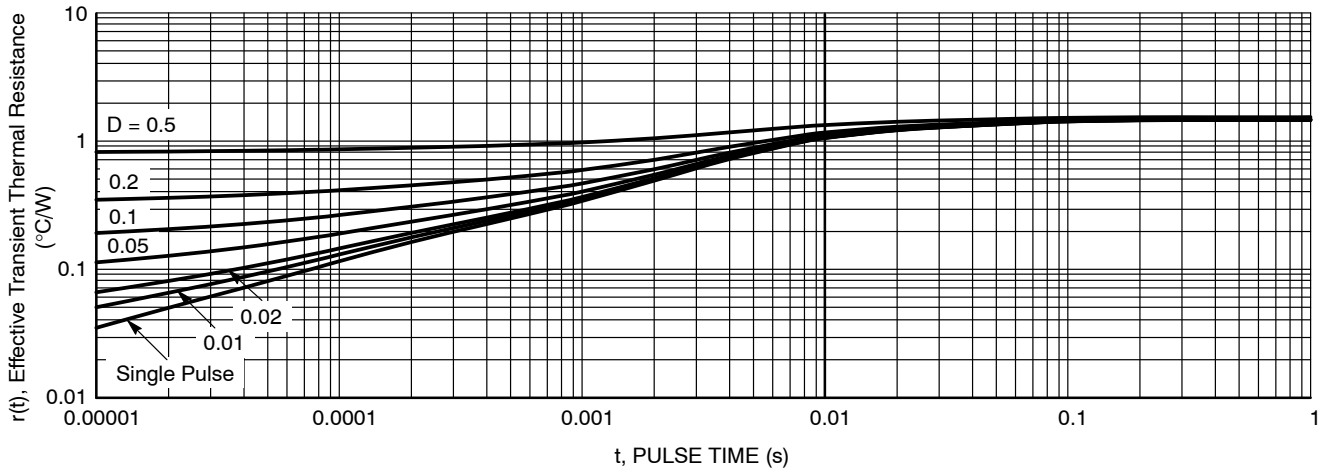


Figure 12. Thermal Response

### ORDERING INFORMATION

Order Number	Package	Shipping†
NTD5802NT4G	DPAK (Pb-Free)	2500 / Tape & Reel
NVD5802NT4G*	DPAK (Pb-Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*NVD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.



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